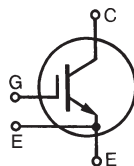


High Voltage IGBT

IXGN100N170

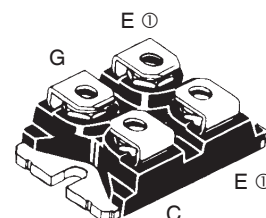
$$\begin{aligned} V_{CES} &= 1700V \\ I_{C90} &= 95A \\ V_{CE(sat)} &\leq 3.0V \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1700	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	160	A
I_{C90}	$T_C = 90^\circ\text{C}$	95	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	600	A
SSOA (RBSOA)	$V_{GE} = 15V, T_{VJ} = 125^\circ\text{C}, R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 200$ @ $0.8 \cdot V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V, V_{CE} = 1250V, T_J = 125^\circ\text{C}$ $R_G = 10\Omega, \text{Non Repetitive}$	10	μs
P_C	$T_C = 25^\circ\text{C}$	735	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60Hz	$t = 1\text{min}$	2500 V~
	$I_{ISOL} \leq 1\text{mA}$	$t = 1\text{s}$	3000 V~
M_d	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
Weight		30	g

SOT-227B, miniBLOC

 E153432



G = Gate, C = Collector, E = Emitter
① either emitter terminal can be used as
Main or Kelvin Emitter

Features

- Optimized for Low Conduction and Switching Losses
- Isolation Voltage 2500V~
- Short Circuit Capability
- International Standard Package
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 3\text{mA}, V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 8\text{mA}, V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			50 μA 3 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 200 nA
$V_{CE(sat)}$	$I_C = 100A, V_{GE} = 15V, \text{Note 1}$		2.5	3.0 V

Symbol Test Conditions

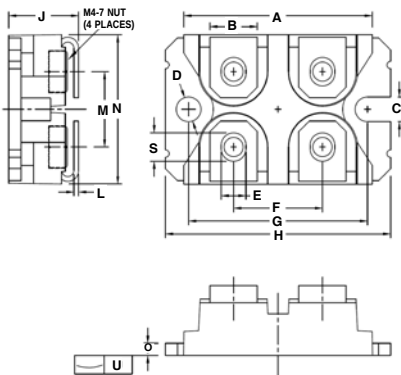
 $(T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	36	64	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		9200	pF
C_{oes}			455	pF
C_{res}			150	pF
Q_g	$I_C = 100\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		425	nC
Q_{ge}			65	nC
Q_{gc}			186	nC
$t_{d(on)}$	Resistive load, $T_J = 25^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$		35	ns
t_r			192	ns
$t_{d(off)}$			285	ns
t_f			395	ns
$t_{d(on)}$	Resistive load, $T_J = 125^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$		35	ns
t_r			250	ns
$t_{d(off)}$			285	ns
t_f			435	ns
R_{thJC}			0.05	0.17°C/W
R_{thCS}				$^\circ\text{C/W}$

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

SOT-227B (IXGN) OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

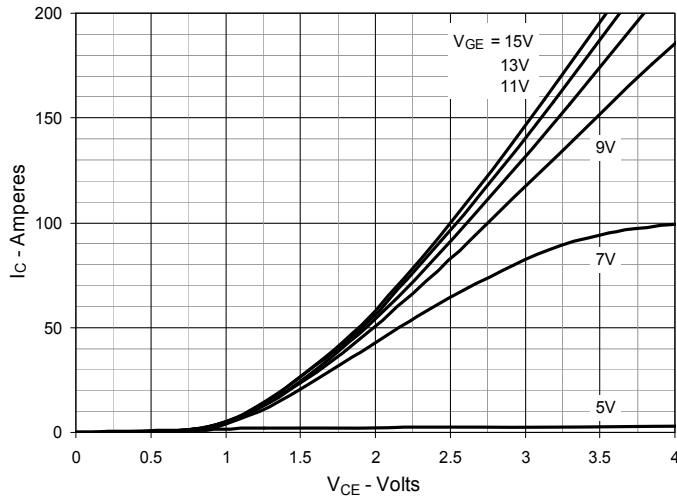
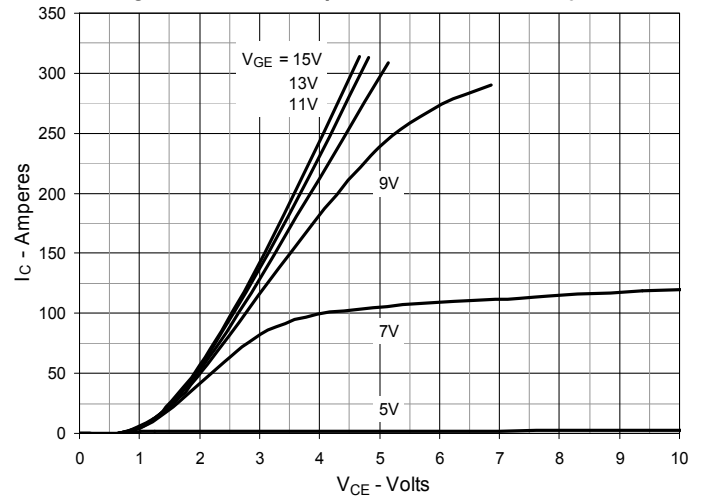
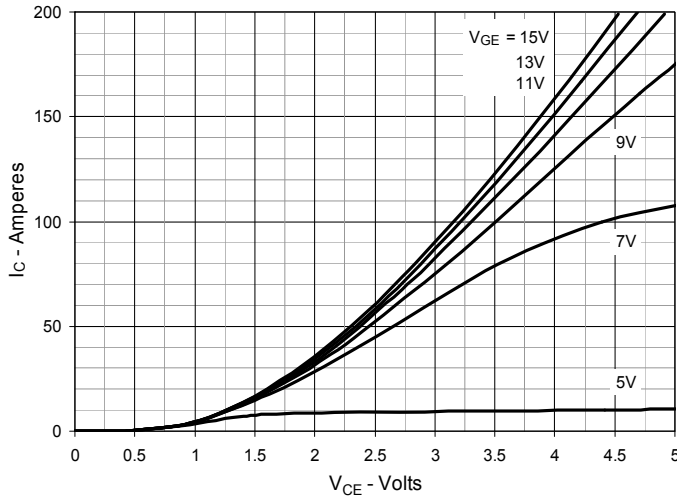
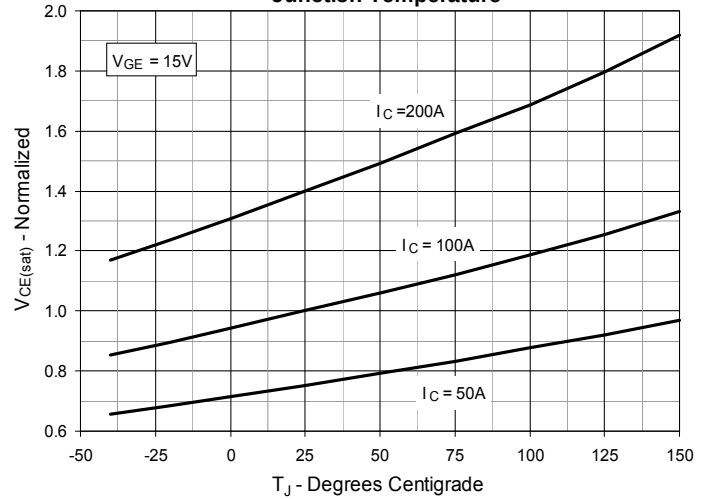
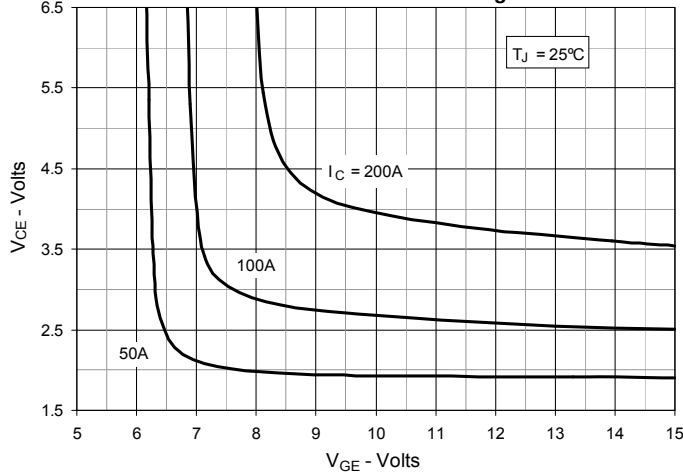
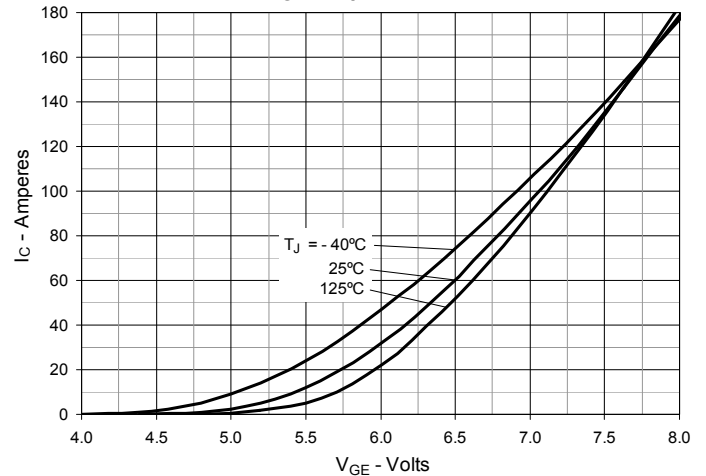
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

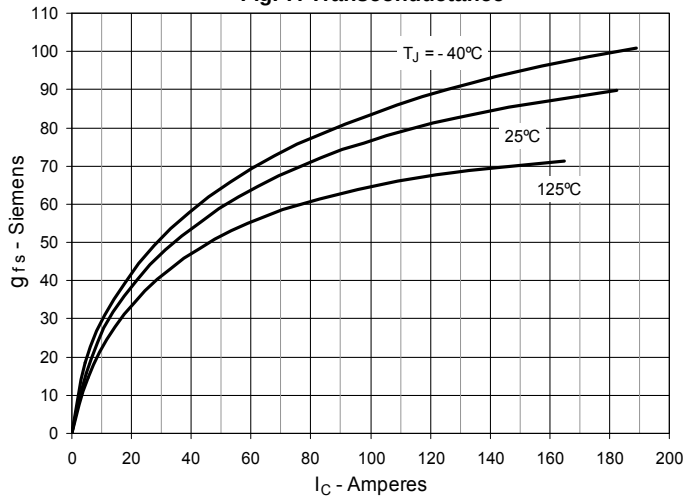


Fig. 8. Gate Charge

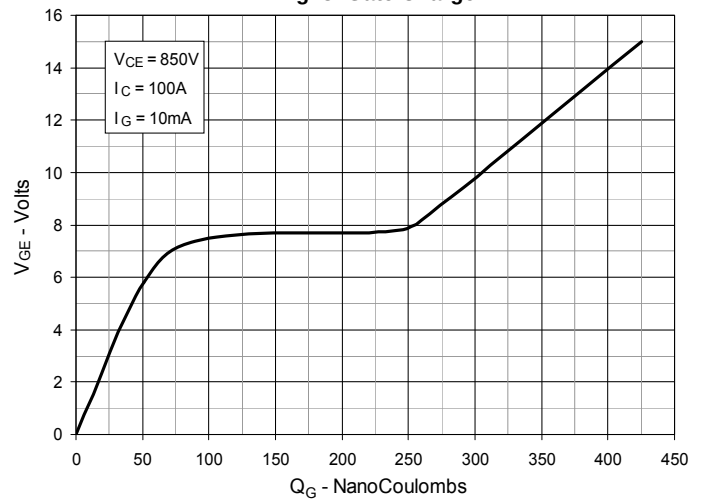


Fig. 9. Reverse-Bias Safe Operating Area

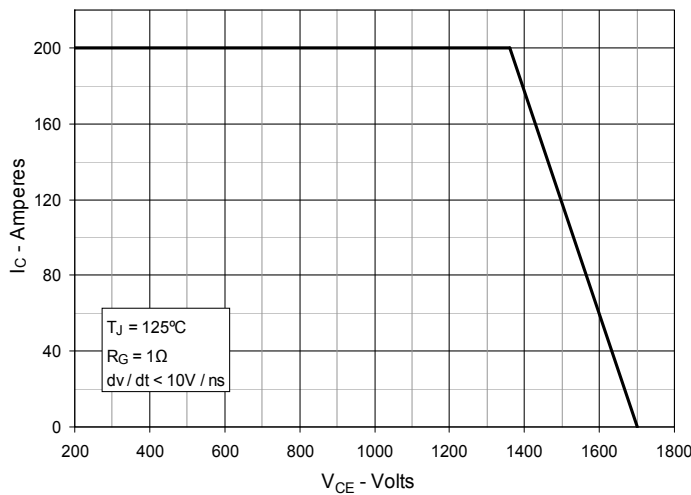


Fig. 10. Capacitance

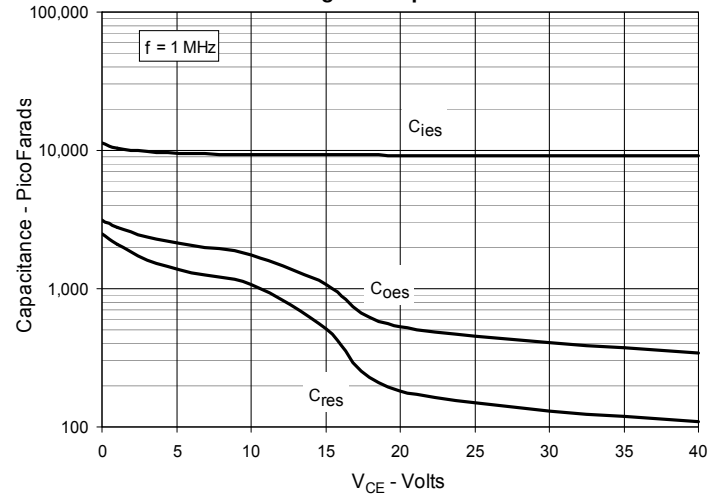


Fig. 11. Maximum Transient Thermal Impedance

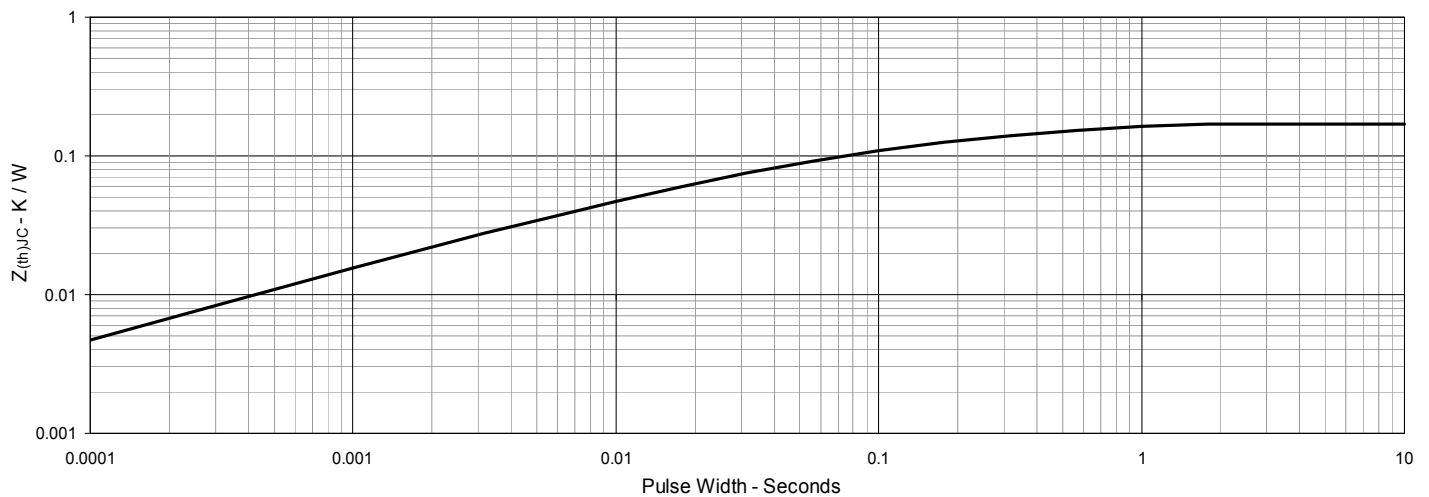
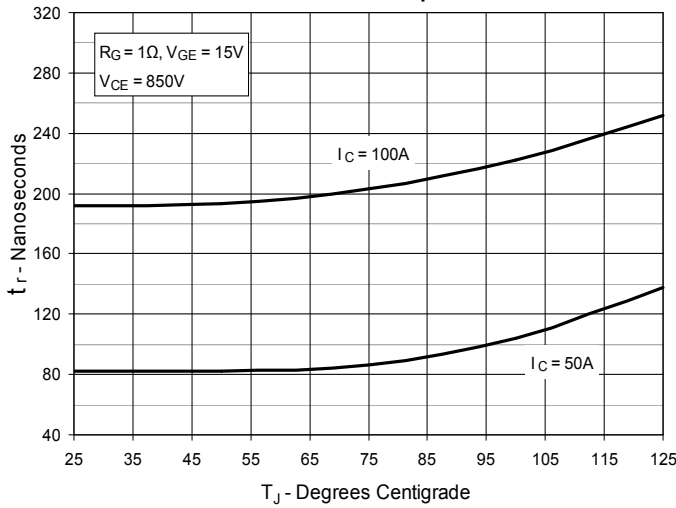
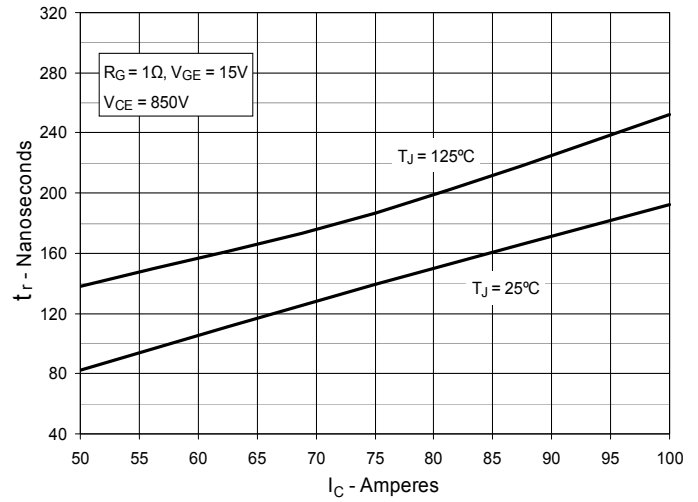
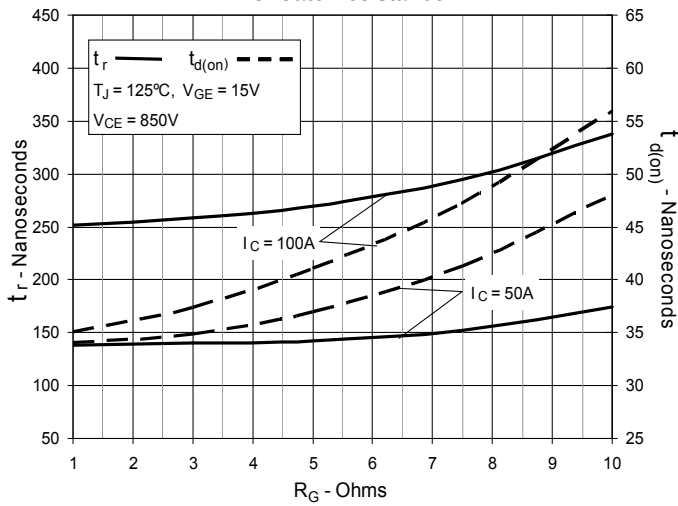
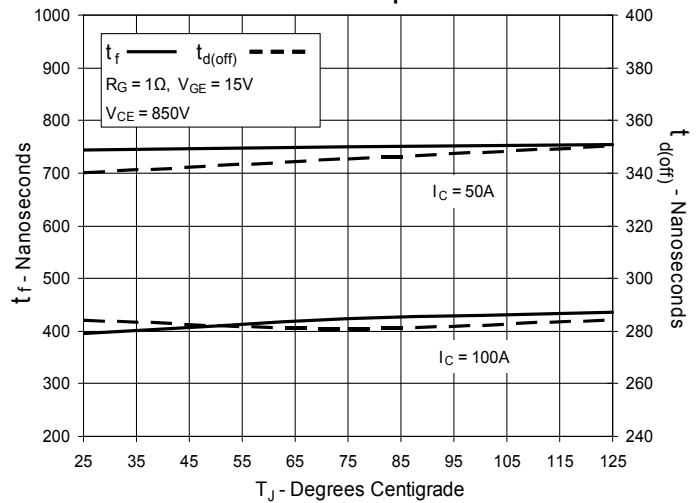
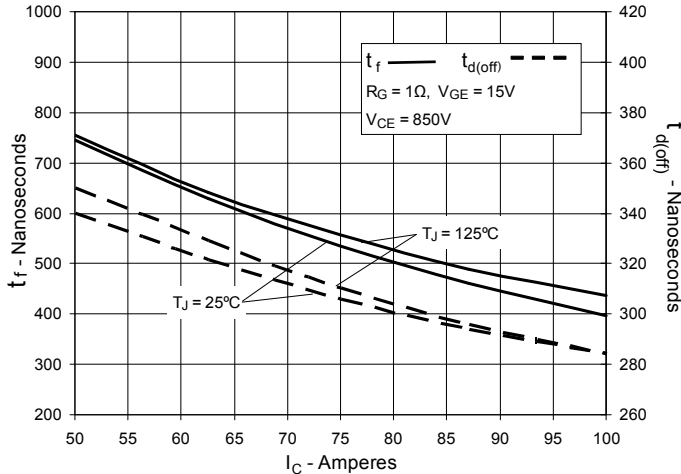
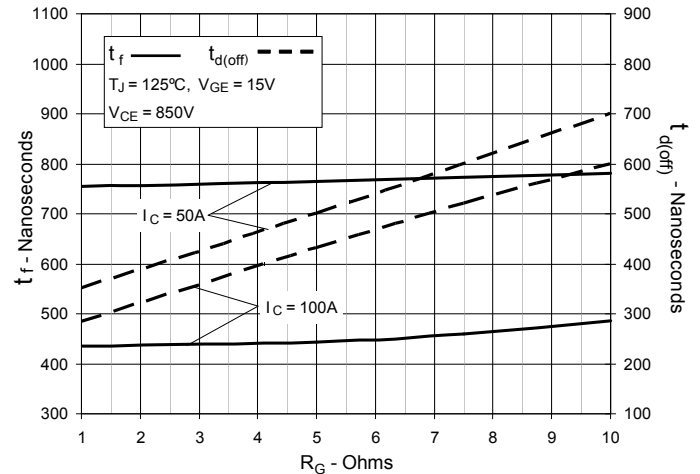


Fig. 12. Resistive Turn-on Rise Time vs. Junction Temperature

Fig. 13. Resistive Turn-on Rise Time vs. Collector Current

Fig. 14. Resistive Turn-on Switching Times vs. Gate Resistance

Fig. 15. Resistive Turn-off Switching Times vs. Junction Temperature

Fig. 16. Resistive Turn-off Switching Times vs. Collector Current

Fig. 17. Resistive Turn-off Switching Times vs. Gate Resistance




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